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RFMD(R) Unveils 400W GaN High Power Amplifier Technology Demonstrator for Pulsed S-band Radar Applications

Paper Presented at IEEE MTT-S International Microwave Symposium 2008

ATLANTA, June 18 /PRNewswire-FirstCall/ -- RF Micro Devices, Inc. (Nasdaq: RFMD), a global leader in the design and manufacture of high-performance semiconductor components, today unveiled a 400W high power amplifier (HPA) that demonstrates the exceptional performance characteristics of RFMD's internally developed gallium nitride (GaN) process technology. The 400W GaN HPAs are designed for air traffic control radar and ship-borne or ground-based pulsed S-band surveillance radar applications.

In radar applications RFMD's 400W GaN HPAs operate over a frequency range of 2.9 to 3.5 GHz, from a 65V supply delivering a power gain of 10.5 dB. Placed in a thermally efficiency, ceramic hermetically sealed package measuring only 24 x 17.4 mm, the 400W GaN HPAs deliver power density and size advantages over competing silicon bipolar technologies. Further, RFMD's GaN process technology provides a larger bandwidth at a higher operating output power than silicon bipolar while maintaining an industry-leading drain efficiency of 50 percent across the band.

Another key area of differentiation for RFMD's GaN is its reliability. In S-band radar applications HPAs are combined in larger 2.5KW "pallet" amplifier assemblies with as many as eight or more HPAs utilized in each pallet. Traveling wave tubes (TWT) technology, traditionally used in these applications, are prone to reliability issues resulting in field failures and expensive replacement costs. With a mean-time-to-failure (MTTF) goal of 1E6 hours at a 200 degrees C junction temperature, RFMD's GaN technology will deliver superior reliability, resulting in a considerably lower total cost of ownership for customers.

"RFMD is committed to delivering a portfolio of highly competitive and compelling components for the aerospace & defense (A&D) marketplace," said Jeff Shealy, vice president and general manager of RFMD's Aerospace & Defense Business Unit. "RFMD's advancements in GaN process technologies are paving the way for a broad range of components for radar and other high power applications. Additionally, our longstanding relationships in the A&D market enable RFMD to engage key customers to evaluate these state-of-the-art process technology innovations."

RFMD's Aerospace & Defense Business Unit has a proven track record of operational excellence and a demonstrated legacy of successful military programs and space program flight history. The Aerospace & Defense Business Unit delivers world-class product innovation and global customer support via multiple design and manufacturing facilities located in North America and Europe. Manufacturing facilities for military and space-level programs are equipped with complete reliability analysis labs as well as in-house screening and qualification. For more information please see www.rfmd.com/aerospacedefense.

RFMD(R) is proud to participate at the IEEE MTT-S International Microwave Symposium 2008 and will present additional information on the 400W GaN HPAs during a technical session at WE1E-01 on Wednesday, June 18th, at 8:00 a.m.

RFMD is showcasing its industry-leading portfolio of high-performance semiconductor components at the IEEE MTT-S International Microwave Symposium 2008, June 17-19, at the Georgia World Congress Center in Atlanta, Georgia, in Booth 1311.

About RFMD: RF Micro Devices, Inc. (Nasdaq GS: RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in quarterly operating results, the rate of growth and development of wireless markets, risks associated with our planned exit from our wireless systems business, including cellular transceivers and GPS solutions, the risk that restructuring charges may be greater than originally anticipated and that the cost savings and other benefits from the restructuring may not be achieved, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

SOURCE RF Micro Devices, Inc.
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CONTACT:
Doug DeLieto, VP, Investor Relations, 1-336-678-7968,
or
Jerry
Neal, Executive Vice President, 1-336-678-7001,
both of RFMD
Web site: http://www.rfmd.com

http://www.rfmd.com/aerospacedefense
(RFMD)